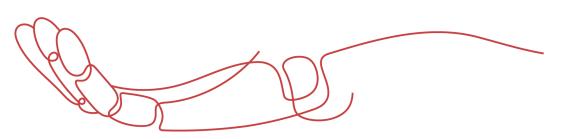




# PRODUCT DATA SHEET



To learn more about JGSEMI, please visit our website at







Datasheet

Sample

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO\_questions@jgsemi.com.



**ESD Protection Diode Array** 

#### **Features**

- 150Watts peak pulse power (tp =  $8/20\mu$ s)
- SOT23-6 package
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Low capacitance (Cj=0.3pF typ. IO to IO)
- Protection one data/power line to:
- IEC 61000-4-2 ±12kV contact ±15kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20μs)



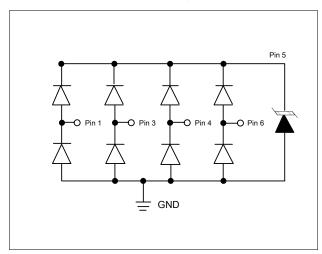
### **Applications**

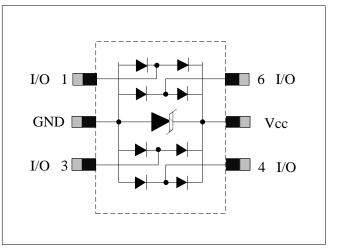
- **■** Ethernet
- Digital Visual Interface (DVI)
- USB2.0
- Notebook and PC Computers

#### **Mechanical Data**

- SOT23-6 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

## Schematic & PIN Configuration







**Absolute Maximum Rating** 

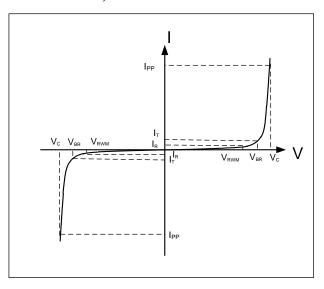
Rating	Symbol	Value	Units	
Peak Pulse Power ( t <sub>p</sub> =8/20μs )	P <sub>PP</sub>	150	Watts	
Peak Pulse Current ( t <sub>p</sub> =8/20μs ) (note1)	$I_{pp}$	5.0	A	
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	$V_{ESD}$	15 12	kV	
Lead Soldering Temperature	$T_{L}$	260(10seconds)	$^{\circ}$ C	
Junction Temperature	$T_{\mathrm{J}}$	-55 to + 125	$^{\circ}$ C	
Storage Temperature	$T_{ m stg}$	-55 to + 125	$^{\circ}$ C	

#### **Electrical Characteristics**

Parameter	Symbol Conditions		Min	Typical	Max	Units
Reverse Stand-Off Voltage	V <sub>RWM</sub>				5.0	V
Reverse Breakdown Voltage	$V_{BR}$	I <sub>T</sub> =1mA	6			V
Reverse Leakage Current	$I_R$	V <sub>RWM</sub> =5V,T=25℃			1.0	uA
Peak Pulse Current	$I_{PP}$	tp =8/20μs			5.0	A
Clamping Voltage	V <sub>C</sub>	$I_{PP}=5.0A, t_p=8/20\mu s$			16	V
Junction Capacitance	$C_{j}$	$V_R = 0V$ , $f = 1MHz$ IO to IO		0.3	0.45	E
		$V_R = 0V$ , $f = 1MHz$ IO to GND		0.6	0.9	pF

# **Electrical Parameters (TA = 25 °C unless otherwise noted)**

Symbol	Parameter
$\mathbf{I}_{PP}$	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ Ipp
V <sub>RWM</sub>	Working Peak Reverse Voltage
IR	Maximum Reverse Leakage Current @ VRWM
$V_{BR}$	Breakdown Voltage @ IT
Іт	Test Current





# **Typical Characteristic Curves**

Fig.1 Peak Pulse Power Rating Curve

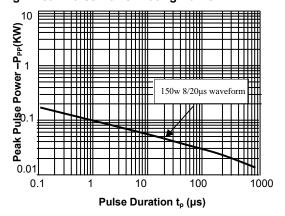


Fig.3 Pulse Waveform-8/20µs

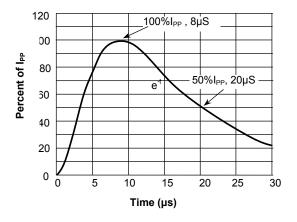


Fig.2 Pulse Derating Curve

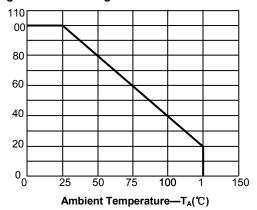
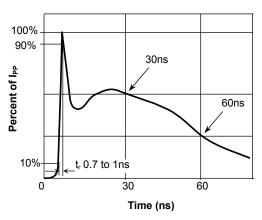


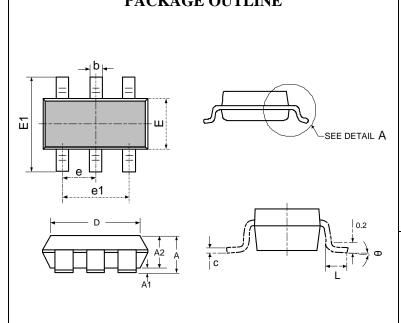
Fig.4 Pulse Waveform-ESD(IEC61000-4-2)





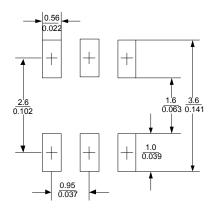
# **Outline Drawing – SOT23-6**

## PACKAGE OUTLINE



DIMENSIONS					
SYMBOL	INCHES		MILLIMETER		
	MIN	MAX	MIN	MAX	
Α	0.041	0.049	1.050	1.250	
A1	0.000	0.004	0.000	0.100	
A2	0.041	0.045	1.050	1.150	
D	0.111	0.119	2.820	3.020	
Е	0.059	0.067	1.500	1.700	
E1	0.104	0.116	2.650	2.950	
b	0.012	0.020	0.300	0.500	
е	0.037(BSC)		0.950(BSC)		
e1	0.071	0.079	1.800	2.000	
L	0.012	0.024	0.300	0.600	
θ	0°	8°	0°	8°	





Notes

1. This land pattern is for reference purposes only consult your manufacturing group to ensure your company's manufacturing guidelines are met.



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